# Supplementary Materials

## Novel Program Scheme of Vertical NAND Flash Memory for Reduction of Z-Interference

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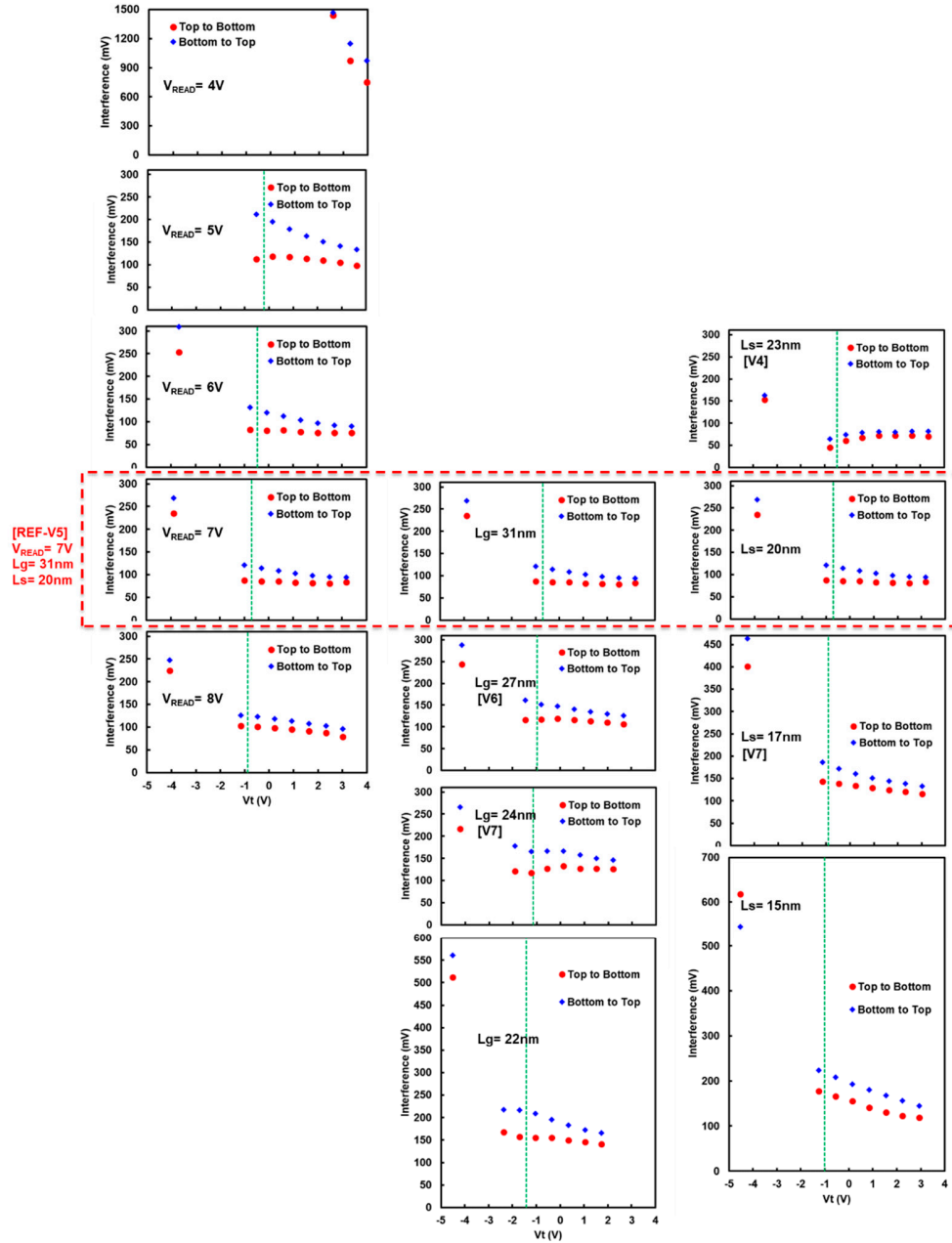
**Figure S1.** Raw data of interference under various conditions of $V_{READ}$, $L_g$, and $L_s$ with respect to the reference $V_{READ}$= 7 V, $L_g$= 31 nm, and $L_s$= 20 nm shown in Figure 5.